

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	252	324/551.ccls.	USPAT	2004/02/18 16:21
2	BRS	5	(US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$).did.	USPAT	2004/02/18 16:14
3	BRS	1	((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$).did.) and ((measur\$3 determin\$3) with resistance)	USPAT	2004/02/18 16:17
4	BRS	3	((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$).did.) and (resistance)	USPAT	2004/02/18 16:18
5	BRS	41	324/554.ccls.	USPAT	2004/02/18 17:17
6	BRS	7	(US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-6433573-\$ or US-6326800-\$).did.	USPAT	2004/02/18 17:29
7	BRS	1	((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-6433573-\$ or US-6326800-\$).did.) and substrate	USPAT	2004/02/18 18:00
8	BRS	452	703/14.ccls.	USPAT	2004/02/18 18:01
9	BRS	0	703/14.ccls. and (breakdown adj resistance)	USPAT	2004/02/19 10:46
10	BRS	1	703/14.ccls. and (breakdown near3 resistance)	USPAT	2004/02/18 18:11
11	BRS	12	("5301084"   "5404041"   "5450267"   "5468667"   "5477414"   "5623387"   "5629545"   "5637892"   "5689133"   "5710689"   "5733794"   "5744841").PN.	USPAT	2004/02/18 18:05
12	BRS	3	5949694.URPN.	USPAT	2004/02/18 18:06
13	BRS	4	324/551.ccls. and (breakdown near3 resistance)	USPAT	2004/05/24 15:32
14	BRS	1	324/554.ccls. and (breakdown near3 resistance)	USPAT	2004/02/18 18:13
15	BRS	4	324/554.ccls. and (insulation near3 resistance)	USPAT	2004/02/19 10:46

	Type	Hits	Search Text	DBs	Time Stamp
16	BRS	137	324/\$.ccls. and (measur\$3 with (insulation near2 resistance))	USPAT	2004/02/18 18:27
17	BRS	65	(324/\$.ccls. and (measur\$3 with (insulation near2 resistance))) and ((measur\$3 with (insulation near2 resistance)) same (voltage and current))	USPAT	2004/02/18 18:28
18	BRS	177	703/4.ccls.	USPAT	2004/02/19 10:43
19	BRS	9	(US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-4360774-\$ or US-6433573-\$ or US-6326800-\$ or US-5949694-\$).did.	USPAT	2004/02/19 10:43
20	BRS	176	703/4.ccls. not ((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-4360774-\$ or US-6433573-\$ or US-6326800-\$ or US-5949694-\$).did.)	USPAT	2004/02/19 10:44
21	BRS	0	(703/4.ccls. not ((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-4360774-\$ or US-6433573-\$ or US-6326800-\$ or US-5949694-\$).did.)) and (insulation near3 resistance)	USPAT	2004/02/19 10:46
22	BRS	0	(703/4.ccls. not ((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-4360774-\$ or US-6433573-\$ or US-6326800-\$ or US-5949694-\$).did.)) and (breakdown adj resistance)	USPAT	2004/02/19 10:46
23	BRS	2	(703/4.ccls. not ((US-5594349-\$ or US-5519324-\$ or US-5420513-\$ or US-5150059-\$ or US-4904946-\$ or US-4360774-\$ or US-6433573-\$ or US-6326800-\$ or US-5949694-\$).did.)) and (parameter adj extraction)	USPAT	2004/02/19 10:50
24	BRS	1	324/698.ccls. and (plural\$3 near3 frequenc\$3)	USPAT	2004/02/19 11:05
25	BRS	1	4701695.pn.	USPAT	2004/02/20 09:47
26	BRS	1	6185705.pn.	USPAT	2004/02/20 09:48
27	BRS	4	324/551.ccls. and (breakdown near3 resistance)	USPAT	2004/05/24 10:01

	Type	Hits	Search T xt	DBs	Time Stamp
28	BRS	68	324/711.ccls.	USPAT	2004/05/24 10:08
29	BRS	0	((critical adj breakdown adj resistance) with (IC semiconductor))	USPAT	2004/05/24 12:13
30	BRS	1	(critical adj breakdown adj resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/24 12:26
31	BRS	1016	(breakdown adj resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/24 12:17
32	BRS	30	((breakdown adj resistance) ) with (IC semiconductor)	USPAT	2004/05/24 12:19
33	BRS	1	((breakdown adj resistance) ) with (IC semiconductor)) and ((measur\$3 determin\$3) with (breakdown adj resistance))	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/05/24 12:18
34	BRS	30	((breakdown adj resistance) ) with (IC semiconductor)	USPAT	2004/05/24 12:20
35	BRS	0	((breakdown adj resistance) ) with 324/\$.ccls.	USPAT	2004/05/24 12:20

	Type	Hits	Search Text	DBs	Time Stamp
36	BRS	0	((breakdown adj resistance) ) with 324/\$.ccls.	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/ 05/24 12:20
37	BRS	4	(702/\$.ccls. and (reliability adj test\$3)) and ((reliability adj test\$3) with (IC semiconductor))	USPAT	2004/ 05/24 15:31
38	BRS	0	((702/\$.ccls. and (reliability adj test\$3)) and ((reliability adj test\$3) with (IC semiconductor))) and (breakdown adj resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/ 05/24 12:26
39	BRS	0	((702/\$.ccls. and (reliability adj test\$3)) and ((reliability adj test\$3) with (IC semiconductor))) and (insulation adj resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/ 05/24 12:27
40	BRS	0	(702/\$.ccls. and (reliability adj test\$3)) and (insulation adj resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/ 05/24 12:27
41	BRS	0	(702/\$.ccls. and (reliability adj test\$3)) and (insulation near2 resistance)	USPAT; US-PG PUB; EPO; JPO; DERWE NT; IBM_T DB	2004/ 05/24 12:27

	Type	Hits	Search Text	DBs	Time Stamp
42	BRS	75	702/\$.ccls. and (reliability adj test\$3)	USPAT	2004/ 05/24 13:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L41	3	702/81.ccls. and (reliability adj (test\$3 evaluation) )	USPAT	2004/05/24 15:31
2	BRS	L42	5	324/765.ccls. and (breakdown near3 resistance)	USPAT	2004/05/24 15:35
3	BRS	L43	1	324/760.ccls. and (breakdown near3 resistance)	USPAT	2004/05/24 15:40
4	BRS	L44	2	324/766.ccls. and (breakdown near3 resistance)	USPAT	2004/05/24 15:40
5	BRS	L45	2	324/691.ccls. and (insulation near3 resistance)	USPAT	2004/05/24 16:08
6	BRS	L46	0	324/452.ccls. and (insulation adj resistance)	USPAT	2004/05/24 16:08
7	BRS	L47	1	324/456.ccls. and (insulation adj resistance)	USPAT	2004/05/24 16:09
8	BRS	L48	1	324/456.ccls. and (insulation adj breakdown)	USPAT	2004/05/24 16:09
9	BRS	L49	0	324/452.ccls. and (insulation adj breakdown)	USPAT	2004/05/24 16:09

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VLSI Technology, 1999. Digest of Technical Papers. 1999 Symposium on , 14 June 1999

Pages:61 - 62

[\[Abstract\]](#)[\[PDF Full-Text \(120 KB\)\]](#)**IEEE CNF****2 Dielectric breakdown mechanism of thin-SiO<sub>2</sub> studied by the post-breakdown resistance statistics***Satake, H.; Toriumi, A.;*

Electron Devices, IEEE Transactions on , Volume: 47 , Issue: 4 , April 2000

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[\[Abstract\]](#)[\[PDF Full-Text \(116 KB\)\]](#)**IEEE JNL****3 Transient effect of DC stressed dielectric breakdown in thin SiO<sub>2</sub>/sil films***Toriumi, A.; Satake, H.;*

Solid-State and Integrated-Circuit Technology, 2001. Proceedings. 6th International Conference on , Volume: 2 , 22-25 Oct. 2001

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[\[Abstract\]](#)[\[PDF Full-Text \(268 KB\)\]](#)**IEEE CNF****4 Aspects of breakdown inhibition in filled composite sites***Williams, P.I.; Dissado, L.A.;*

Conduction and Breakdown in Solid Dielectrics, 1995. ICSD'95., Proceedings of 1995 IEEE 5th International Conference on , 10-13 July 1995

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[\[Abstract\]](#) [\[PDF Full-Text \(204 KB\)\]](#) [IEEE CNF](#)

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**5 Enhanced dielectric breakdown lifetime of the copper/silicon nitride/silicon dioxide structure**

*Takeda, K.-I.; Hinode, K.; Oodake, I.; Ohashi, N.; Yamaguchi, H.;*

Reliability Physics Symposium Proceedings, 1998. 36th Annual. 1998 IEEE International , 31 March-2 April 1998

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[\[Abstract\]](#) [\[PDF Full-Text \(456 KB\)\]](#) [IEEE CNF](#)

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